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International Rectifier (Infineon Technologies Americas Corp.)
IRLR8103TR

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International
IOR Rectifier

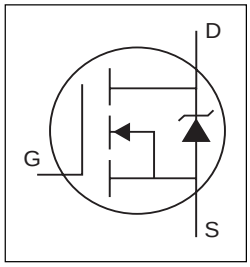
PD - 93838
PD - 93839

IRLR8103/IRLR8503

Provisional Data Sheet

- N-Channel Application-Specific MOSFETs
- Ideal for CPU Core DC-DC Converters
- Low Conduction Losses
- Low Switching Losses
- Minimizes Parallel MOSFETs for high current applications

HEXFET® Chipset for DC-DC Converters



D-Pak

Description

These new devices employ advanced HEXFET® power MOSFET technology to achieve an unprecedented balance of on-resistance and gate charge. The reduced conduction and switching losses make them ideal for high efficiency DC-DC converters that power the latest generation of microprocessors.

Both the IRLR8103 and IRLR8503 have been optimized and are 100% tested for all parameters that are critical in synchronous buck converters including $R_{DS(on)}$, gate charge and Cdv/dt-induced turn-on immunity. The IRLR8103 offers particulary low $R_{DS(on)}$ and high Cdv/dt immunity for synchronous FET applications. The IRLR8503 offers an extremely low combination of Q_{sw} & $R_{DS(on)}$ for reduced losses in control FET applications.

The package is designed for vapor phase, infrared, convection, or wave soldering techniques. Power dissipation of greater than 80W is possible in a typical PCB mount application.

DEVICE RATINGS (typ.)

	IRLR8103	IRLR8503
V_{DS}	30V	30V
$R_{DS(on)}$	6 mΩ	12 mΩ
Q_G	45 nC	15 nC
Q_{sw}	20.3 nC	5.4 nC
Q_{oss}	23 nC	23 nC

Absolute Maximum Ratings

Parameter		Symbol	IRLR8103	IRLR8503	Units
Drain-Source Voltage		V_{DS}	30		V
Gate-Source Voltage		V_{GS}	±20		
Continuous Drain or Source Current ($V_{GS} \geq 10V$)	T_A = 25°C	I_D	89⑤	49⑤	A
	T_L = 90°C		61⑤	34⑤	
Pulsed Drain Current①		I_{DM}	350	196	
Power Dissipation	T_A = 25°C	P_D	89	62	W
	T_L = 90°C		42	30	
Junction & Storage Temperature Range		T_J, T_{STG}	–55 to 150		°C
Continuous Source Current (Body Diode)		I_S	89⑤	49⑤	A
Pulsed Source Current①		I_{SM}	350	196	

Thermal Resistance

Parameter		Max.		Units
Maximum Junction-to-Ambient PCB③	$R_{\theta JA}$	50		°C/W
Maximum Junction-to-Case	$R_{\theta JC}$	1.4	2.0	°C/W

Electrical Characteristics

Parameter		IRLR8103 Min	IRLR8103 Typ	IRLR8103 Max	IRLR8503 Min	IRLR8503 Typ	IRLR8503 Max	Units	Conditions
Drain-to-Source Breakdown Voltage*	BV_{DSS}	30	–	–	30	–	–	V	V_{GS} = 0V, I_D = 250µA
Static Drain-Source on Resistance*	$R_{DS(ON)}$	–	6	7.0		12	16	mΩ	V_{GS} = 10V, I_D = 15A②
		–	7	8.5		14	18	mΩ	V_{GS} = 4.5V, I_D = 15A②
Gate Threshold Voltage*	$V_{GS(th)}$	2.0	–	–	1.0	–	–	V	V_{DS} = V_{GS}, I_D = 250µA
Drain-Source Leakage Current*	I_{DSS}	–	–	30	–	–	30	µA	V_{DS} = 24V, V_{GS} = 0
		–	–	150	–	–	150		V_{DS} = 24V, V_{GS} = 0, Tj = 100°C
Gate-Source Leakage Current*	I_{GSS}	–	–	±100	–	–	±100	nA	V_{GS} = ±20V
Total Gate Chg Cont FET*	Q_G	–	50	–	–	15	–	nC	V_{GS}=5V, I_D=15A, V_{DS}=16V
Total Gate Chg Sync FET*	Q_G	–	45	–	–	13	–		V_{GS} = 5V, V_{DS}< 100mV
Pre-Vth Gate-Source Charge	Q_{GS1}	–	17	–	–	3.7	–		V_{DS} = 16V, I_D = 15A
Post-Vth Gate-Source Charge	Q_{GS2}	–	4.3	–	–	1.3	–		
Gate to Drain Charge	Q_{GD}	–	16	–	–	4.1	–		
Switch Chg(Q_{gs2} + Q_{gd})*	Q_{SW}	–	20.3	–	–	5.4	–		
Output Charge*	Q_{oss}	–	23	–	–	23	–		V_{DS} = 16V, V_{GS} = 0
Gate Resistance	R_G	–	1.5	–	–	2.0	–	Ω	
Turn-on Delay Time	t_d(on)	–	TBD	–	–	TBD	–	ns	V_{DD} = 16V, I_D = 15A
Rise Time	t_r	–	TBD	–	–	TBD	–		V_{GS} = 5V
Turn-off Delay Time	t_d (off)	–	TBD	–	–	TBD	–		Clamped Inductive Load
Fall Time	t_f	–	TBD	–	–	TBD	–		See test diagram Fig 19.
Input Capacitance	C_{iss}	–	TBD	–	–	TBD	–	pF	V_{DS} = 16V, V_{GS} = 0
Output Capacitance	C_{oss}	–	TBD	–	–	TBD	–		
Reverse Transfer Capacitance	C_{rss}	–	TBD	–	–	TBD	–		

Source-Drain Rating & Characteristics

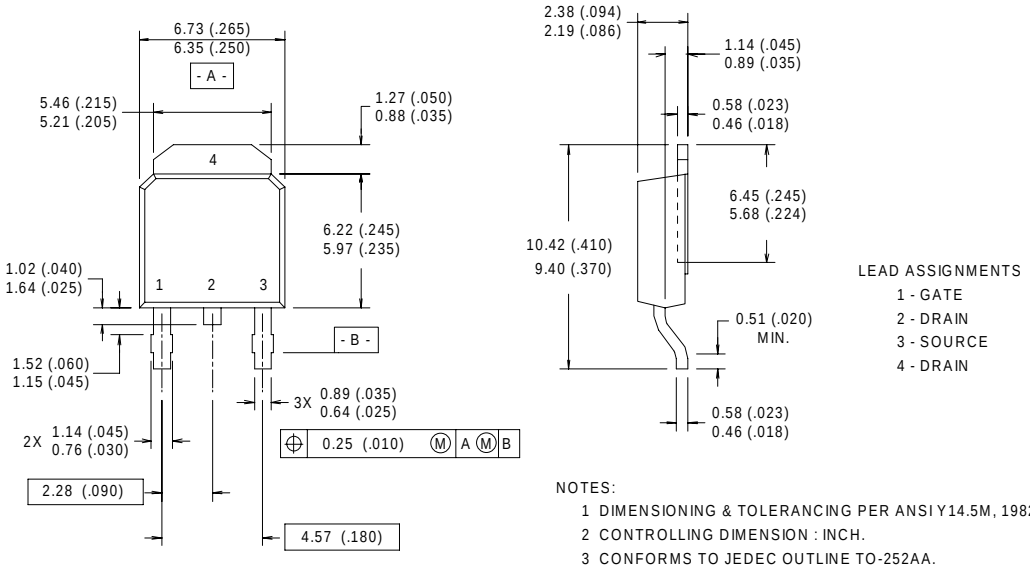
Parameter		Min	Typ	Max	Min	Typ	Max	Units	Conditions
Diode Forward Voltage*	V_{SD}	–	–	0.9	–	–	1.0	V	I_S = 15A②, V_{GS} = 0V
Reverse Recovery Charge④	Q_{rr}	–	100	–	–	89	–	nC	di/dt ~ 700A/µs V_{DS} = 16V, V_{GS} = 0V, I_S = 15A
Reverse Recovery Charge (with Parallel Schottky)④	$Q_{rr(s)}$	–	77	–	–	75	–		di/dt = 700A/µs (with 10BQ040) V_{DS} = 16V, V_{GS} = 0V, I_S = 15A

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.
② Pulse width ≤ 300 µs; duty cycle ≤ 2%.
③ When mounted on 1 inch square copper board, t < 10 sec.
④ Typ = measured - Q_{oss}
⑤ Calculated continuous current based on maximum allowable Junction temperature; packagle limitation current = 20A
* Devices are 100% tested to these parameters.

Package Outline

TO-252AA Outline
Dimensions are shown in millimeters (inches)

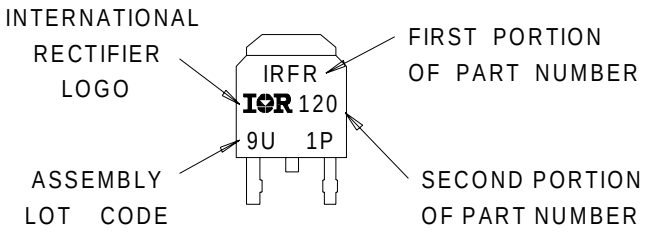


NOTES:
1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
2 CONTROLLING DIMENSION : INCH.
3 CONFORMS TO JEDEC OUTLINE TO-252AA.
4 DIMENSIONS SHOWN ARE BEFORE SOLDER DIP, SOLDER DIP MAX. +0.16 (.006).

Part Marking Information

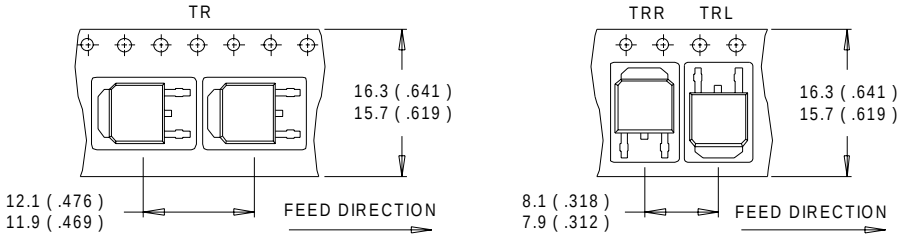
TO-252AA (D-PARK)

EXAMPLE : THIS IS AN IRFR120
WITH ASSEMBLY
LOT CODE 9U1P

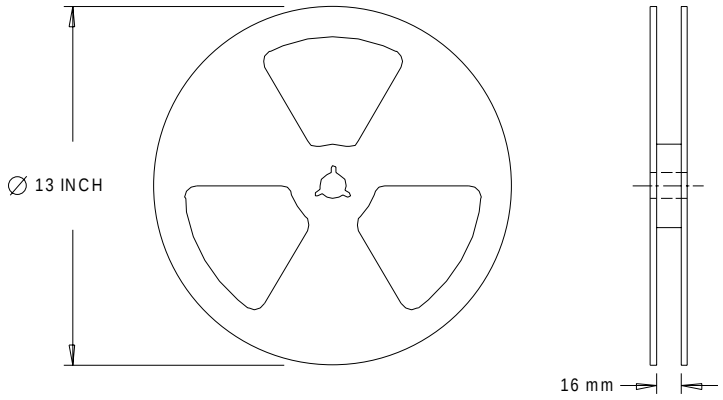


Tape & Reel Information

TO-252AA



NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :
1. OUTLINE CONFORMS TO EIA-481.

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